

Solid State Power Amplifier 20 to 2500MHz MODEL BHED27258-200

Features:

- GaN Technology for Ultra Wideband Operation
 - 20 – 1000MHz, 125W
 - 1000 – 2500MHz, 200W
- Integrated T/R Switch for Each Band
- Compact Configuration
- Simultaneous Operation of Both Bands



Performance Specifications

- Frequency Range: 20 to 2500MHz in two bands
- RF Power Out (after T/R Switches):
 - Band 1 (20-1000MHz) 125 Watts Typical
 - Band 2 (1000-2500MHz) 200 Watts Typical
- RF Input: 0 dBm; ± 3 dB Typical
- RF input Overdrive: 8 dBm Max.
- Class of Operation: AB Linear
- Modulation Format: Multi-tone, CW, AM, FM, SSB Pulse
- VSWR: 2.0:1 with 0.5dB turndown
3:0:1 and higher with appropriate turndown
- Harmonic Rejection: <-13 dBc Typical
- Spurious: <-60 dBc
- AM Distortion (85% DOM): 10% max
- T/R Isolation: 50dB
- T/R Switching Speed: 50 μ sec
- Noise Power Output:
 - Transmit Mode: -86dBm/Hz typical
 - Receive Mode (NQ ON): -150dBm/Hz
- Noise Quieting Speed: 10 μ sec

- Digital Display: Forward Power, Reflected Power, Fault Status, VSWR, Thermal Fault, PA Status, PS Status
- Control Interface: RS-422, Ethernet
- Local Indicators: Thermal Fault, T/R Status, Power On
- Internal Protection: Load VSWR; Overdrive: Over-Current; Hot Switch; Thermal Overload
- Primary Power: 110/220VAC; 50/60Hz
- Power Consumption: 1850W
- RF Connectors:
 - RF Input and receive Ports: N Type female
 - RF Output: N Type female
- Environmental:
 - Operating Temperature: -10° to +55°C
 - Operating Altitude: 10,000 feet
 - Shock/Vibration: MIL-STD-810G
- Size: 5U high (8.75")
- Weight: 60 lbs.

Comtech PST (CPST) is pleased to introduce Model BHED27258-200, a compact, efficient dual band 20-2500MHz solid state high power amplifier. This highly integrated design utilizes the latest GaN technology; which achieves one of the highest power density-to-footprint ratios of amplifier building blocks throughout the industry.